

μ A759 • μ A77000

Power Operational Amplifiers

Linear Division Operational Amplifiers

Description

The μ A759 and μ A77000 are high performance monolithic operational amplifiers constructed using the Fairchild Planar Epitaxial process. The μ A759 provides 325 mA and the μ A77000 provides 250 mA output current and feature small signal characteristics better than the μ A741. The amplifiers are designed to operate from a single or dual power supply with the input common mode range including the negative supply. The high gain and high output power provide superior performance whenever an operational amplifier is needed. The μ A759 and μ A77000 employ internal current limiting, thermal shutdown, and safe-area compensation making them essentially indestructible. These amplifiers are intended for a wide range of applications including voltage regulators, audio amplifiers, servo amplifiers, and power drivers.

- Output Current

μ A759 — 325 mA Minimum
 μ A77000 — 250 mA Minimum

- Internal Short Circuit Current Limiting

- Internal Thermal Overload Protection

- Internal Output Transistors Safe-Area Protection

- Input Common Mode Voltage Range Includes Ground Or Negative Supply

Absolute Maximum Ratings

Storage Temperature Range

Metal Can	-65°C to +175°C
Power Watt	-65°C to +150°C

Operating Junction Temperature Range

Extended (μ A759M)	-55 to +150°C
Commercial (μ A759C, μ A77000C)	0°C to +125°C

Lead Temperature

Metal Can (soldering, 60 s)	300°C
Power Watt (soldering, 10 s)	265°C

Internal Power Dissipation¹

Internally Limited

Supply Voltage

\pm 18 V

Differential Input Voltage

30 V

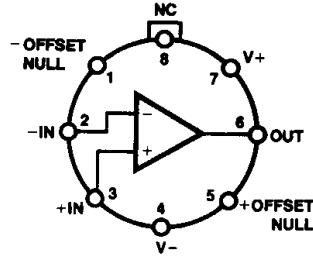
Input Voltage²

\pm 15 V

Notes

1. Although the internal power dissipation is limited, the junction temperature must be kept below the maximum specified temperature in order to meet data sheet specifications. To calculate the maximum junction temperature or heat sink required, use the thermal resistance values which follow the Electrical Characteristics Table.
2. For a supply voltage less than 30 V between V+ and V-, the absolute maximum input voltage is equal to the supply voltage.

Connection Diagram 8-Lead Metal Package (Top View)



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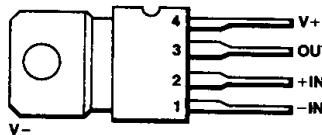
Lead 4 connected to case.

Order Information

Device Code	Package Code	Package Description
μ A759HM	5W	Metal
μ A759HC	5W	Metal

Connection Diagram

TO-202 Package (Top View)

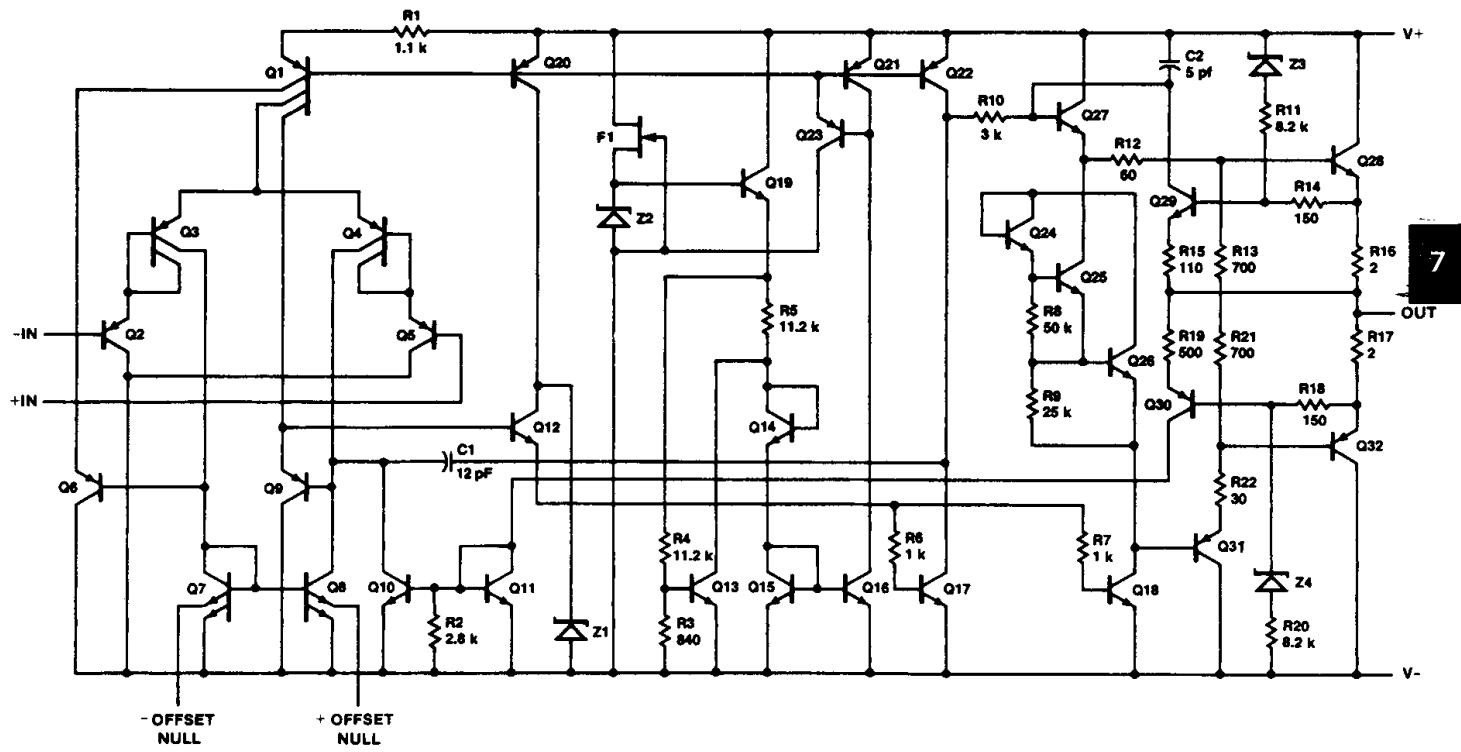


CD00500F

Order Information

Device Code	Package Code	Package Description
μ A759U1C	8Z	Power Watt
μ A77000U1C	8Z	Power Watt

Equivalent Circuit



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EQ00021F

Note

All resistor values in ohms.

μ A759

Electrical Characteristics $T_J = 25^\circ\text{C}$, $V_{CC} = \pm 15 \text{ V}$, unless otherwise specified.

Symbol	Characteristic		Condition	Min	Typ	Max	Unit
V_{IO}	Input Offset Voltage		$R_S \leq 10 \text{ k}\Omega$		1.0	3.0	mV
I_{IO}	Input Offset Current				5.0	30	nA
I_{IB}	Input Bias Current				50	150	nA
Z_I	Input Impedance			0.25	1.5		$M\Omega$
I_{CC}	Supply Current				12	18	mA
V_{IR}	Input Voltage Range			+13 to V_-	+13 to V_-		V
I_{OS}	Output Short Circuit Current		$ V_{CC} - V_O = 30 \text{ V}$		± 200		mA
$I_{O PEAK}$	Peak Output Current		$3.0 \text{ V} \leq V_{CC} - V_O \leq 10 \text{ V}$	± 325	± 500		mA
A_{VS}	Large Signal Voltage Gain		$R_L \geq 50 \text{ }\Omega$, $V_O = \pm 10 \text{ V}$	50	200		V/mV
TR	Transient Response	Rise time	$R_L = 50 \text{ }\Omega$, $A_V = 1.0$		300		ns
		Overshoot			5.0		%
SR	Slew Rate		$R_L = 50 \text{ }\Omega$, $A_V = 1.0$		0.6		V/ μ s
BW	Bandwidth		$A_V = 1.0$		1.0		MHz

The following specifications apply for $-55^\circ\text{C} \leq T_J \leq +150^\circ\text{C}$

V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			4.5	mV
I_{IO}	Input Offset Current				60	nA
I_{IB}	Input Bias Current				300	nA
CMR	Common Mode Rejection	$R_S \leq 10 \text{ k}\Omega$	80	100		dB
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	80	100		dB
A_{VS}	Large Signal Voltage Gain	$R_L \geq 50 \text{ }\Omega$, $V_O = \pm 10 \text{ V}$	25	200		V/mV
V_{OP}	Output Voltage Swing	$R_L = 50 \text{ }\Omega$	± 10	± 12.5		V

μ A759C

Electrical Characteristics $T_J = 25^\circ\text{C}$, $V_{CC} = \pm 15$ V, unless otherwise specified.

Symbol	Characteristic		Condition	Min	Typ	Max	Unit
V_{IO}	Input Offset Voltage		$R_S \leq 10 \text{ k}\Omega$		1.0	6.0	mV
I_{IO}	Input Offset Current				5.0	50	nA
I_{IB}	Input Bias Current				50	250	nA
Z_I	Input Impedance			0.25	1.5		$M\Omega$
I_{CC}	Supply Current				12	18	mA
V_{IR}	Input Voltage Range			+13 to V_-	+13 to V_-		V
I_{OS}	Output Short Circuit Current		$ V_{CC} - V_O = 30$ V		± 200		mA
$I_{O PEAK}$	Peak Output Current		$3.0 \text{ V} \leq V_{CC} - V_O \leq 10 \text{ V}$	± 325	± 500		mA
A_{VS}	Large Signal Voltage Gain		$R_L \geq 50 \Omega$, $V_O = \pm 10$ V	25	200		V/mV
TR	Transient Response	Rise time	$R_L = 50 \Omega$, $A_V = 1.0$		300		ns
		Overshoot			10		%
SR	Slew Rate		$R_L = 50 \Omega$, $A_V = 1.0$		0.5		V/ μ s
BW	Bandwidth		$A_V = 1.0$		1.0		MHz

The following specifications apply for $0^\circ \leq T_J \leq +125^\circ\text{C}$

V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			7.5	mV
I_{IO}	Input Offset Current				100	nA
I_{IB}	Input Bias Current				400	nA
CMR	Common Mode Rejection	$R_S \leq 10 \text{ k}\Omega$	70	100		dB
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$	80	100		dB
A_{VS}	Large Signal Voltage Gain	$R_L \geq 50 \Omega$, $V_O = \pm 10$ V	25	200		V/mV
V_{OP}	Output Voltage Swing	$R_L = 50 \Omega$	± 10	± 12.5		V

μ A77000

Electrical Characteristics $T_J = 25^\circ\text{C}$, $V_{CC} = \pm 15 \text{ V}$, unless otherwise specified.

Symbol	Characteristic		Condition	Min	Typ	Max	Unit
V_{IO}	Input Offset Voltage		$R_S \leq 10 \text{ k}\Omega$		1.0	8.0	mV
I_{IO}	Input Offset Current				5.0	50	nA
I_{IB}	Input Bias Current				50	250	nA
Z_I	Input Impedance			0.25	1.5		M Ω
I_{CC}	Supply Current				12	18	mA
V_{IR}	Input Voltage Range			+13 to V-	+13 to V-		V
I_{OS}	Output Short Circuit Current		$ V_{CC} - V_O = 30 \text{ V}$		± 200		mA
$I_{O PEAK}$	Peak Output Current		$3.0 \text{ V} \leq V_{CC} - V_O \leq 10 \text{ V}$	± 250	± 400		mA
A_{VS}	Large Signal Voltage Gain		$R_L \geq 50 \text{ }\Omega$, $V_O = \pm 10 \text{ V}$	25	200		V/mV
TR	Transient Response	Rise time	$R_L = 50 \text{ }\Omega$, $A_V = 1.0$		300		ns
		Overshoot			10		%
SR	Slew Rate		$R_L = 50 \text{ }\Omega$, $A_V = 1.0$		0.5		V/ μ s
BW	Bandwidth		$A_V = 1.0$		1.0		MHz

The following specifications apply for $0^\circ \leq T_J \leq +125^\circ\text{C}$

V_{IO}	Input Offset Voltage	$R_S \leq 10 \text{ k}\Omega$			10	mV
I_{IO}	Input Offset Current				100	nA
I_{IB}	Input Bias Current				400	nA
CMR	Common Mode Rejection	$R_S \leq 10 \text{ k}\Omega$		70	100	dB
PSRR	Power Supply Rejection Ratio	$R_S \leq 10 \text{ k}\Omega$		80	100	dB
A_{VS}	Large Signal Voltage Gain	$R_L \geq 50 \text{ }\Omega$, $V_O = \pm 10 \text{ V}$		25	200	V/mV
V_{OP}	Output Voltage Swing	$R_L = 50 \text{ }\Omega$		± 10	± 12.5	V

Package	Typ	Max	Typ	Max
	θ_{JC} °C/W	θ_{JC} °C/W	θ_{JA} °C/W	θ_{JA} °C/W
Power Watt (U1)	8.0	12	75	80
Metal Can (H)	30	40	120	150

$$P_{D\ Max} = \frac{T_J\ Max - T_A}{\theta_{JC} + \theta_{CA}} \text{ or}$$

$$= \frac{T_J\ Max - T_A}{\theta_{JA}} \text{ (Without a heat sink)}$$

$$\theta_{CA} = \theta_{CS} + \theta_{SA}$$

Solving T_J :

$$T_J = T_A + P_D(\theta_{JC} + \theta_{CA}) \text{ or}$$

$$= T_A + P_D\theta_{JA} \text{ (Without a heat sink)}$$

Where:

T_J = Junction Temperature

T_A = Ambient Temperature

P_D = Power Dissipation

θ_{JA} = Junction to ambient thermal resistance

θ_{JC} = Junction to case thermal resistance

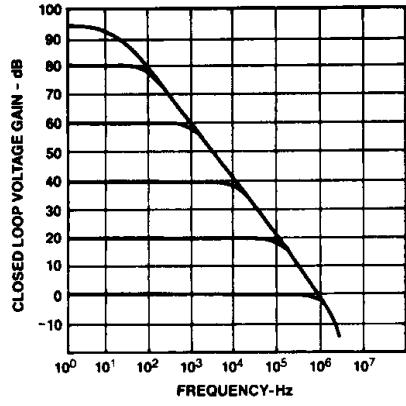
θ_{CA} = Case to ambient thermal resistance

θ_{CS} = Case to heat sink thermal resistance

θ_{SA} = Heat sink to ambient thermal resistance

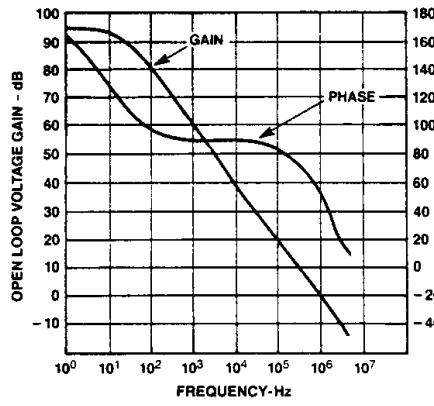
Typical Performance Curves

Frequency Response For Various Closed Loop Gains

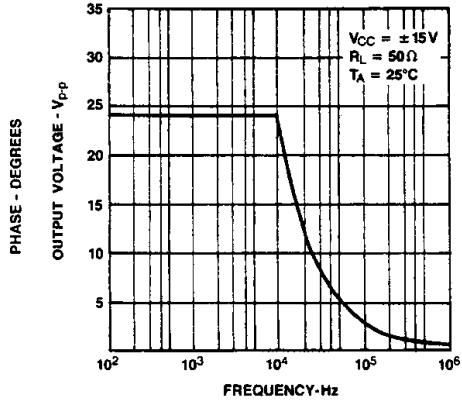


PC02471F

Open Loop vs Frequency Response



Output Voltage vs Frequency



PC02480F

Mounting Hints

Metal Can Package (μ A759HC/ μ A759HM)

The μ A759 in the 8-Lead TO-99 metal can package must be used with a heat sink. With ± 15 V power supplies, the μ A759 can dissipate up to 540 mW in its quiescent (no load) state. This would result in a 100°C rise in chip temperature to 125°C (assuming a 25°C ambient temperature). In order to avoid this problem, it is advisable to use either a slip on or stud mount heat sink with this package. If a stud mount heat sink is used, it may be necessary to use insulating washers between the stud and the chassis because the case of the μ A759 is internally connected to the negative power supply terminal.

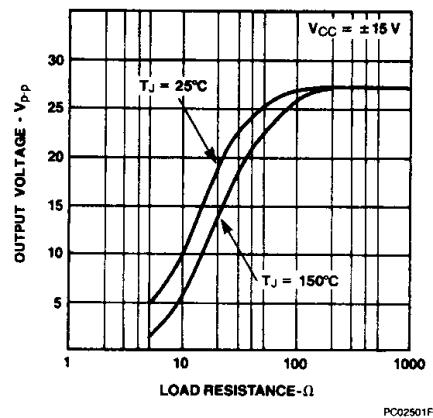
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Power Watt Package (μ A759U1C/ μ A77000U1C)

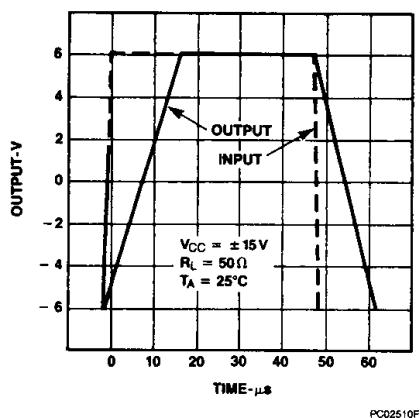
The μ A759U1C and μ A77000U1C are designed to be attached by the tab to a heat sink. This heat sink can be either one of the many heat sinks which are commercially available, a piece of metal such as the equipment chassis, or a suitable amount of copper foil as on a double sided PC board. The important thing to remember is that the negative power supply connection to the op amp must be made through the tab. Furthermore, adequate heat sinking must be provided to keep the chip temperature below 125°C under worst case load and ambient temperature conditions.

Typical Performance Curves (Cont.)

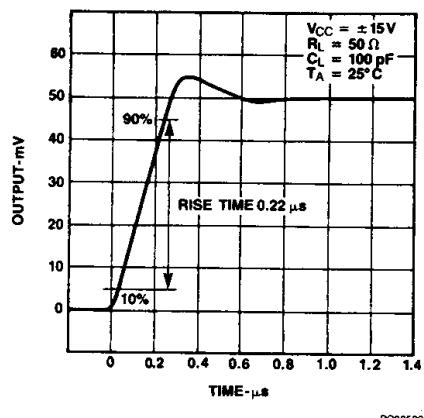
Output Voltage vs Load Resistance



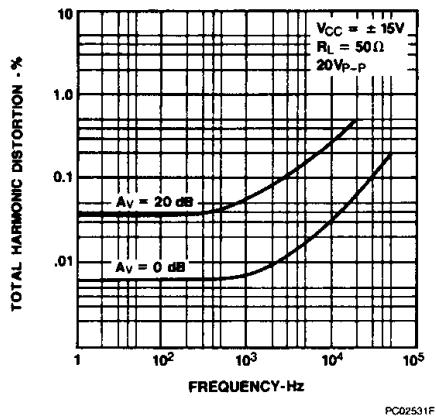
Voltage Follower Large Signal Pulse Response



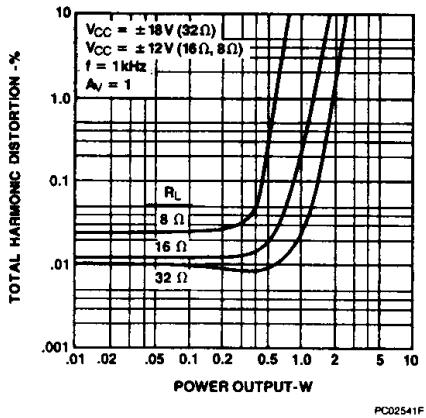
Voltage Follower Transient Response



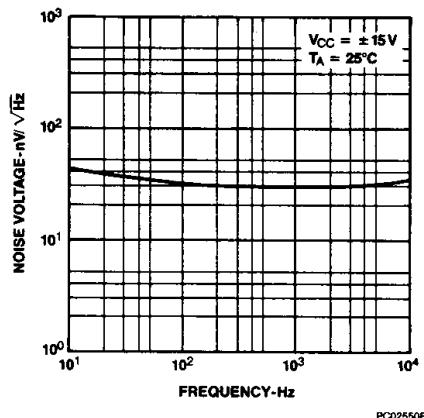
Total Harmonic Distortion vs Frequency



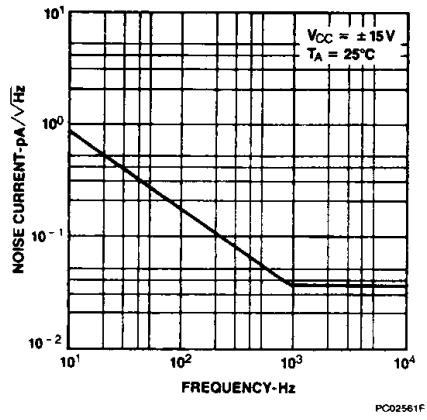
Total Harmonic Distortion vs Power Output



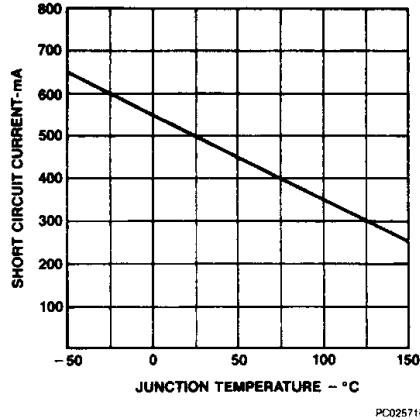
Input Noise Voltage vs Frequency



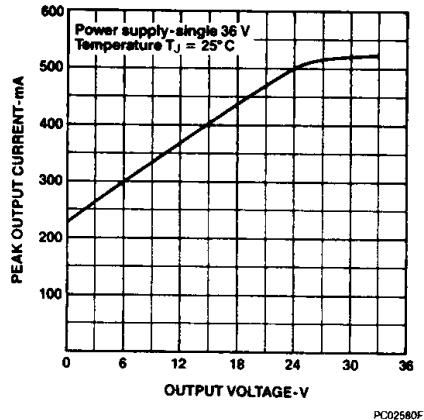
Noise Current vs Frequency



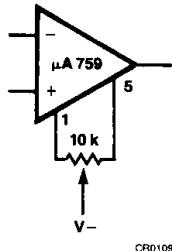
Short Circuit Current vs Junction Temperature



Peak Output Current vs Output Voltage

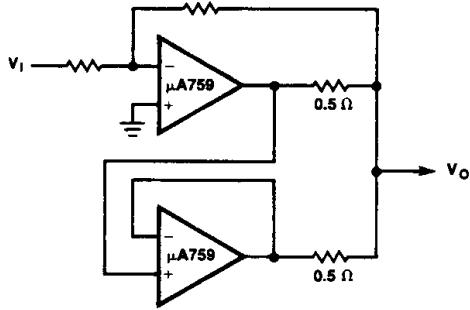


Offset Null Circuit



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Paralleling μ A759 Power Op Amps

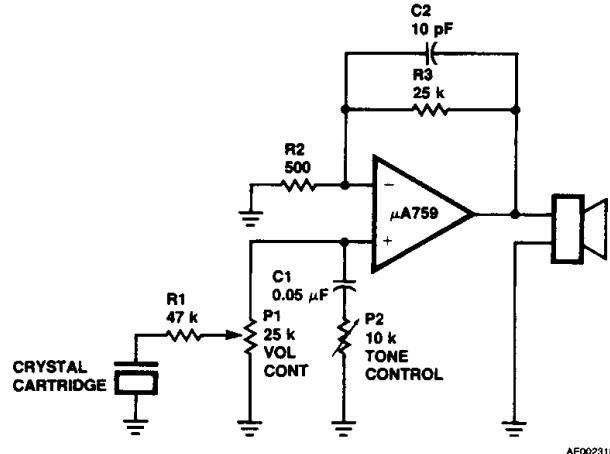


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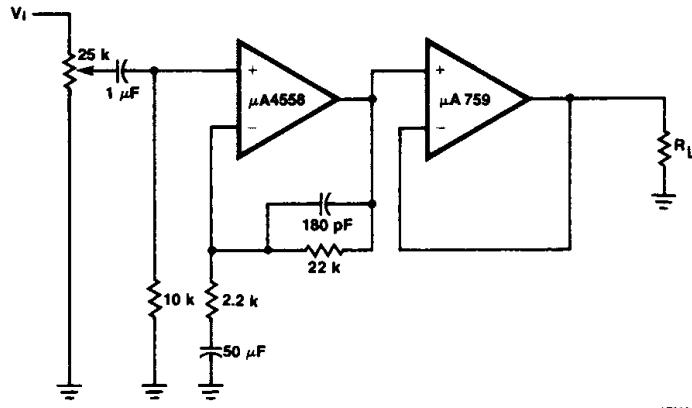
Audio Applications

Low Cost Phono Amplifier



Speaker Impedance (ohms)	Output Power (watts)	Min Supply (volts)	V_{Op-p} (volts)
4	.18	9	2.4
8	.36	12	4.8
16	.72	15	9.6
32	1.44	25	19.2

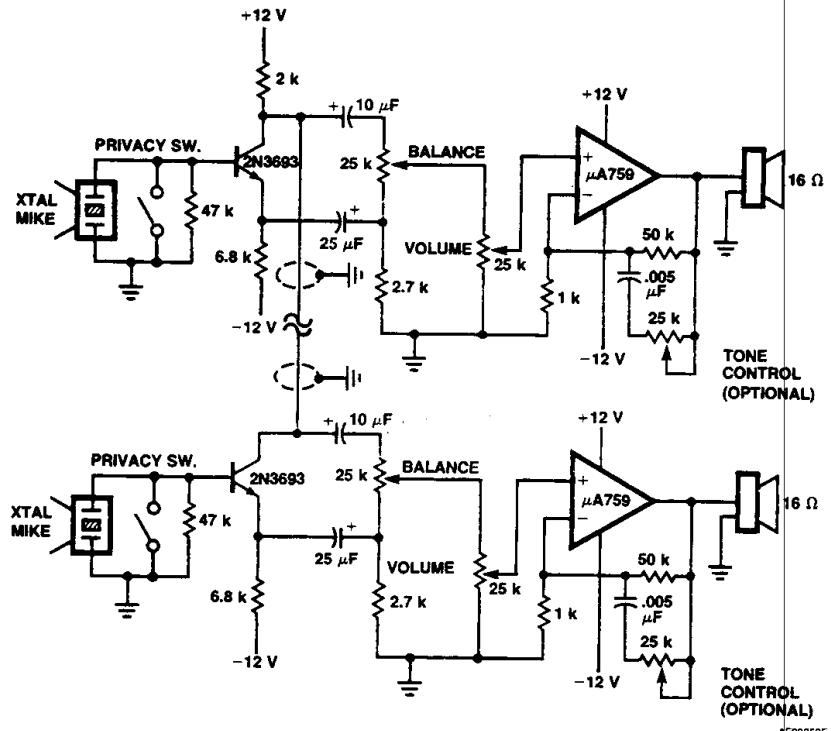
Headphone Amplifier



Note

1. All resistor values in ohms.

**Bi-Directional Intercom System Using
the μ A759 Power Op Amp**



AF00250F

Features

Circuit Simplicity

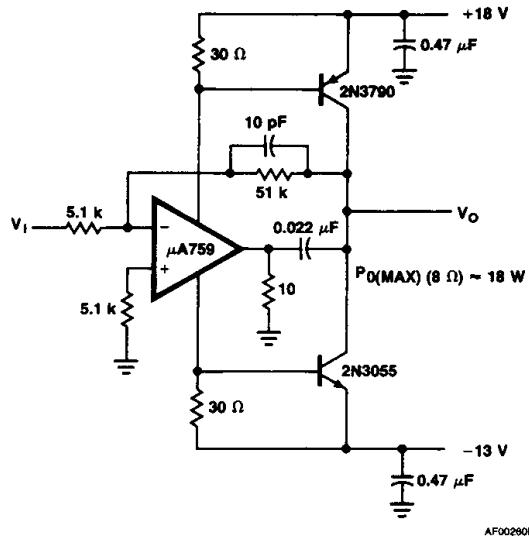
1 Watt of Audio Output

Duplex operation with only one two-wire cable as
interconnect.

Note

1. All resistor values in ohms.

High Slew Rate Power OP Amp/Audio Amp



Features

High Slew Rate $9 \text{ V}/\mu\text{s}$

High 3 dB Power Bandwidth 85 kHz

18 Watts Output Power Into an 8Ω Load.

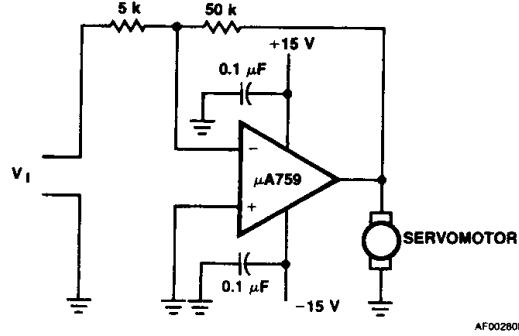
Low Distortion — .2%, 10 VRMS, 1 kHz Into 8Ω

Design Consideration

$$A_V \geq 10$$

Servo Applications

DC Servo Amplifiers



Features

Circuit Simplicity

One Chip Means Excellent Reliability

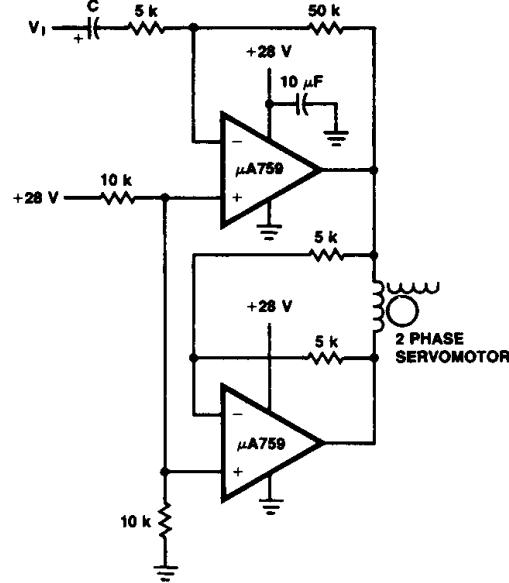
Design Considerations

$$I_O \leq 325 \text{ mA}$$

Note

1. All resistor values in ohms.

AG Servo Amplifier – Bridge Type



Features

Gain of 10

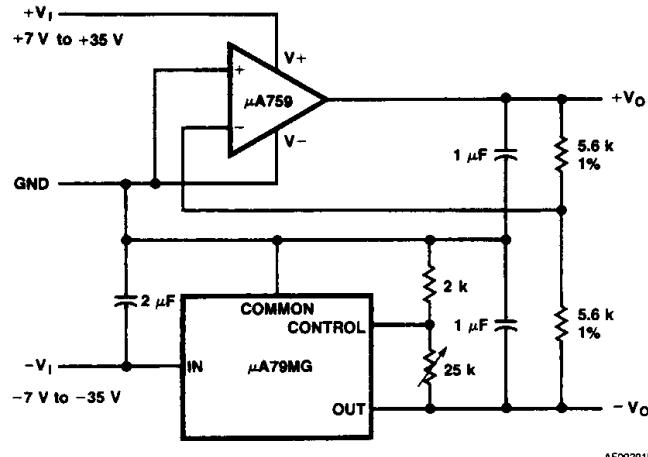
Use of μ A759 Means Simple Inexpensive Circuit

Design Considerations

325 mA Max Output Current

Regulator Applications

Adjustable Dual Tracking Regulator



AF00291F

Features

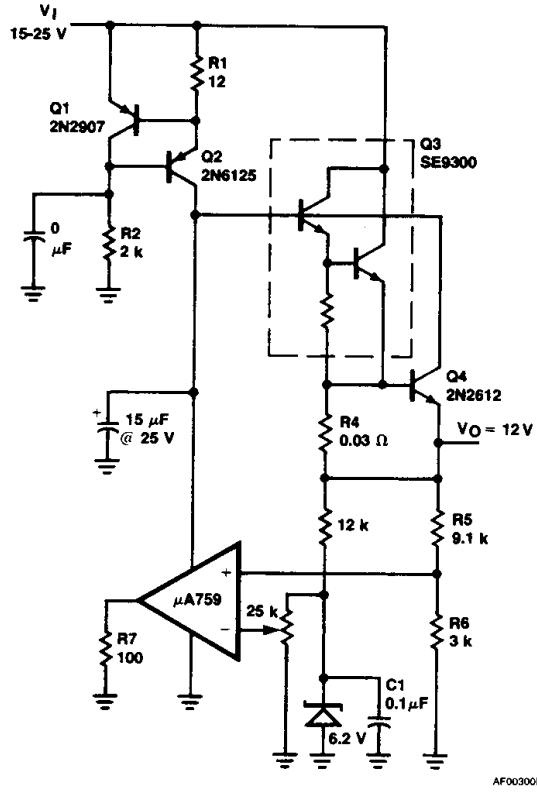
- Wide Output Voltage Range (± 2.2 to ± 30 V)
- Excellent Load Regulation $\Delta V_O < \pm 5$ mV for $\Delta I_O = \pm 0.2$ A
- Excellent Line Regulation $\Delta V_O < \pm 2$ mV for $\Delta V_I = 10$ V

Note

1. All resistor values in ohms.

Regulator Applications (Cont.)

10 Amp – 12 Volt Regulator



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Features

- Excellent Load and Line Regulation
- Excellent Temperature Coefficient-Depends largely on Tempco of the Reference Zener

Note

1. All resistor values in ohms.